

6-BIT, 1-of-2 MULTIPLEXER/DEMULTIPLEXER WITH INTEGRATED IEC L-4 ESD AND 1.8-V LOGIC COMPATIBLE CONTROL INPUTS

Check for Samples: [TS3A27518E-Q1](#)

FEATURES

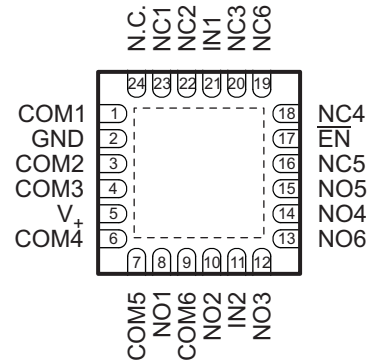
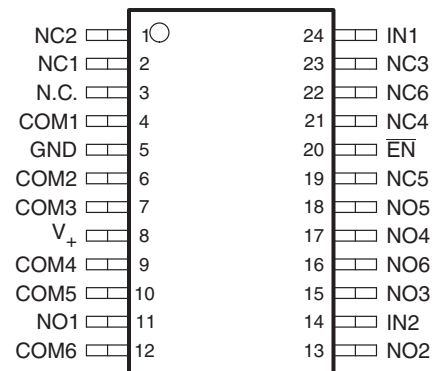
- Qualified for Automotive Applications
- AEC-Q100 Qualified With the Following Results:
 - Device Temperature Grade 2: –40°C to 105°C Ambient Operating Temperature Range
 - Device HBM ESD Classification Level H2
 - Device CDM ESD Classification Level C3B
- 1.65-V to 3.6-V Single-Supply Operation
- Isolation in Powerdown Mode, $V_+ = 0$
- Low Capacitance Switches, 21.5 pF (Typical)
- Bandwidth up to 240 MHz for High-Speed Rail-to-Rail Signal Handling
- Crosstalk and Off Isolation of -62dB
- 1.8-V Logic Threshold Compatibility for Control Inputs
- 3.6-V Tolerant Control Inputs
- ESD Performance: NC/NO Ports
 - ±6-kV Contact Discharge (IEC 61000-4-2)
- 24-Pin TSSOP (7,9-mm × 6,6-mm) and 24-Pin QFN (4-mm × 4-mm) Package

APPLICATIONS

- SD/SDIO and MMC Two Port MUX
- PC VGA Video MUX/Video Systems
- Audio and Video Signal Routing

DESCRIPTION

The TS3A27518E-Q1 is a 6-bit 1-of-2 mux/demux designed to operate from 1.65 V to 3.6 V. This device can handle both digital and analog signals, and signals up to V_+ can be transmitted in either direction. The TS3A27518E-Q1 has two control pins, each controlling three 1-of-2 muxes at the same time, and an enable pin that is used to put all outputs in high-impedance mode. The control pins are compatible with 1.8-V logic thresholds and are backward compatible with 2.5-V and 3.3-V logic thresholds as well.

**RTW PACKAGE
(TOP VIEW)**

**PW PACKAGE
(TOP VIEW)**


N.C. – Not internally connected



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

DESCRIPTION (CONTINUED)

The TS3A27518E-Q1 allows any SD, SDIO, and multimedia card host controllers to be expanded out to multiple cards or peripherals because the SDIO interface consists of 6-bits: CMD, CLK, and Data[0:3] signals. The TS3A27518E-Q1 has two control pins that give additional flexibility to the user, for example, the ability to mux two different audio-video signals in equipment such as an LCD television, an LCD monitor, or a notebook docking station.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾ (2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	TSSOP – PW	Reel of 2000	TS3A27518EIPWRQ1	YL518EQ1
	QFN – RTW	Reel of 3000	TS3A27518EIRTWRQ1	27518EI
–40°C to 105°C	QFN-RTW	Reel of 3000	TS3A27518ETRTWRQ1	27518T

- (1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (2) For the most-current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

LOGIC DIAGRAM

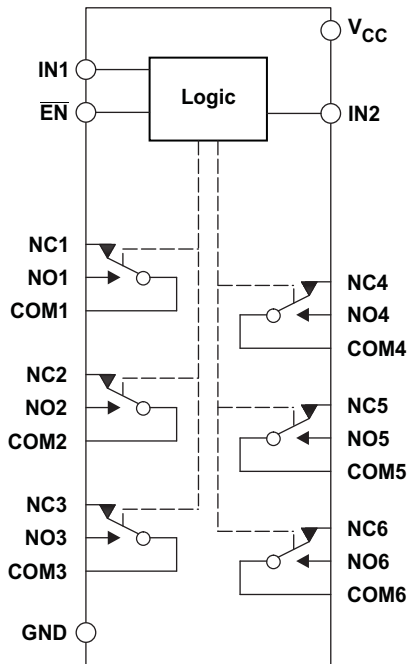


Table 1. SUMMARY OF CHARACTERISTICS

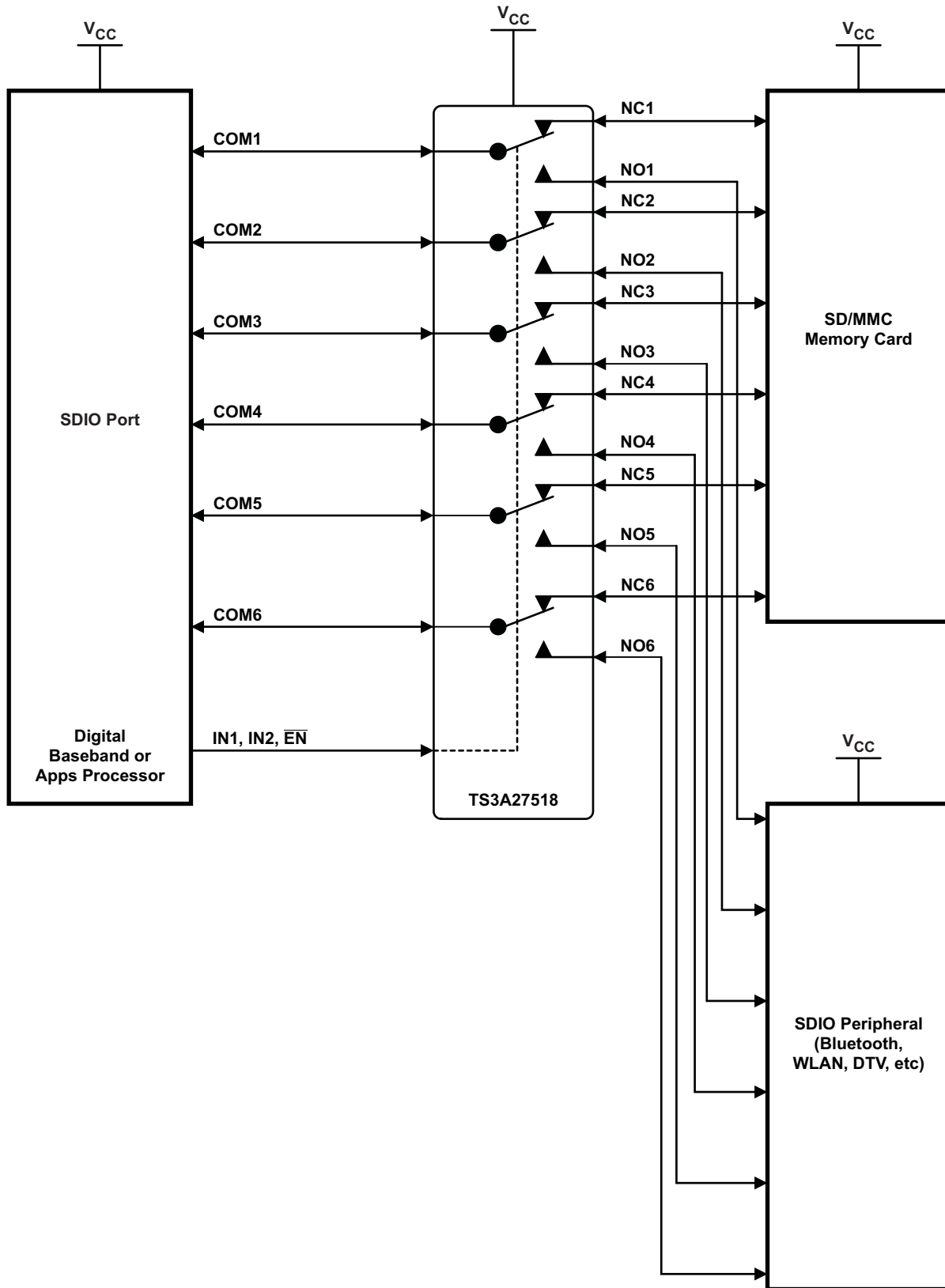
V₊ = 3.3 V, T_A = 25°C

Configuration	1-of-2 Multiplexer/Demultiplexer
Number of channels	6
ON-state resistance (r _{on})	6.2 Ω (max)
ON-state resistance match (Δr _{on})	0.7 Ω (max)
ON-state resistance flatness (r _{ON(flat)})	2.1 Ω (max)
Turn-on/turn-off time (t _{ON} /t _{OFF})	59 ns/ 60.6 ns (max)
Break-before-make time (t _{BBM})	22.7 ns (max)
Charge injection (Q _C)	0.81 pC
Bandwidth (BW)	240 MHz
OFF isolation (O _{ISO})	–62 dB at 10 MHz
Crosstalk (X _{TALK})	–62 dB at 10 MHz
Total harmonic distortion (THD)	0.05%
Power-supply current (I ₊)	< 0.3 μA (max)
Package options	24-pin QFN (RTW), 24-BGA (ZQS) 24-TSSOP (PW)

Table 2. FUNCTION TABLE

\overline{EN}	IN1	IN2	NC1/2/3 TO COM1/2/3, COM1/2/3 TO NC1/2/3	NC4/5/6 TO COM4/5/6, COM4/5/6 TO NC4/5/6	NO1/2/3 TO COM1/2/3, COM1/2/3 TO NO1/2/3	NO4/5/6 TO COM4/5/6, COM4/5/6 TO NO4/5/6
H	X	X	OFF	OFF	OFF	OFF
L	L	L	ON	ON	OFF	OFF
L	H	L	OFF	ON	ON	OFF
L	L	H	ON	OFF	OFF	ON
L	H	H	OFF	OFF	ON	ON

SDIO EXPANDER APPLICATION BLOCK DIAGRAM



ABSOLUTE MINIMUM AND MAXIMUM RATINGS^{(1) (2)}

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT	
V ₊	Supply voltage range ⁽³⁾	-0.5	4.6	V	
V _{NC} V _{NO} V _{COM}	Analog voltage range ^{(3) (4) (5)}	-0.5	4.6	V	
I _K	Analog port diode current ⁽⁶⁾	V ₊ < V _{NC} , V _{NO} , V _{COM} < 0		mA	
I _{INC} I _{INO} I _{ICOM}	ON-state switch current ⁽⁷⁾	V _{NC} , V _{NO} , V _{COM} = 0 to V ₊		mA	
V _I	Digital input voltage range ^{(3) (4)}	-0.5	4.6	V	
I _{IK}	Digital input clamp current ^{(3) (4)}	V _{IO} < V _I < 0		mA	
I ₊	Continuous current through V ₊		100	mA	
I _{GND}	Continuous current through GND	-100		mA	
T _{stg}	Storage temperature range	-65	150	°C	
ESD rating		Human-body model (HBM) AEC-Q100 Classification Level H2		2	kV
		Charged-device model (CDM) AEC-Q100 Classification Level C3B		750	V

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Requires clamp diodes on analog port to V₊.
- (7) Pulse at 1-ms duration <10% duty cycle

THERMAL IMPEDANCE RATINGS

			UNIT
θ _{JA}	Package thermal impedance ⁽¹⁾	PW package	87.9
		RTW	66

- (1) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾

V₊ = 3 V to 3.6 V, T_A = -40°C to 105°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	V _{COM} , V _{NO} , V _{NC}				0		V ₊	Ω
ON-state resistance	r _{on}	0 ≤ (V _{NC} or V _{NO}) ≤ V ₊ , I _{COM} = -32 mA, Switch ON, See Figure 15	25°C	3 V		4.4	6.2	Ω
			Full			7.6		
ON-state resistance match between channels	Δr _{on}	V _{NC} or V _{NO} = 2.1 V, I _{COM} = -32 mA, Switch ON, See Figure 15	25°C	3 V		0.3	0.7	Ω
			Full			0.8		
ON-state resistance flatness	r _{on(flat)}	0 ≤ (V _{NC} or V _{NO}) ≤ V ₊ , I _{COM} = -32 mA, Switch ON, See Figure 16	25°C	3 V		0.95	2.1	Ω
			Full			2.3		

- (1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾ (continued)
 $V_+ = 3\text{ V to }3.6\text{ V}$, $T_A = -40^\circ\text{C to }105^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT	
NC, NO OFF leakage current	$I_{NC(OFF)}$, $I_{NO(OFF)}$	V_{NC} or $V_{NO} = 1\text{ V}$, $V_{COM} = 3\text{ V}$, or V_{NC} or $V_{NO} = 3\text{ V}$, $V_{COM} = 1\text{ V}$,	Switch OFF, See Figure 16	25°C	3.6 V	-0.5	0.05	0.5	μA
				Full		-7		7	
	$I_{NC(PWROFF)}$, $I_{NO(PWROFF)}$	V_{NC} or $V_{NO} = 0\text{ to }3.6\text{ V}$, $V_{COM} = 3.6\text{ V to }0$, or V_{NC} or $V_{NO} = 3.6\text{ V to }0$, $V_{COM} = 0\text{ to }3.6\text{ V}$,	25°C	0 V	-1	0.05	1		
			Full		-12		12		
COM OFF leakage current	$I_{COM(OFF)}$	V_{NC} or $V_{NO} = 3\text{ V}$, $V_{COM} = 1\text{ V}$, or V_{NC} or $V_{NO} = 1\text{ V}$, $V_{COM} = 3\text{ V}$,	Switch OFF, See Figure 16	25°C	3.6 V	-1	0.01	1	μA
				Full		-2		2	
	$I_{COM(PWROFF)}$	V_{NC} or $V_{NO} = 3.6\text{ V to }0$, $V_{COM} = 0\text{ to }3.6\text{ V}$, or V_{NC} or $V_{NO} = 0\text{ to }3.6\text{ V}$, $V_{COM} = 3.6\text{ V to }0$,	25°C	0 V	-1	0.02	1		
			Full		-12		12		
NC, NO ON leakage current	$I_{NO(ON)}$, $I_{NC(ON)}$	V_{NC} or $V_{NO} = 1\text{ V}$, $V_{COM} = \text{Open}$, or V_{NC} or $V_{NO} = 3\text{ V}$, $V_{COM} = \text{Open}$,	Switch ON, See Figure 17	25°C	3.6 V	-2.5	0.04	2.2	μA
				-40°C to 85°C		-7		7	
				85°C to 105°C		-7.5		7.5	
COM ON leakage current	$I_{COM(ON)}$	V_{NC} or $V_{NO} = \text{Open}$, $V_{COM} = 1\text{ V}$, or V_{NC} or $V_{NO} = \text{Open}$, $V_{COM} = 3\text{ V}$,	Switch ON, See Figure 17	25°C	3.6 V	-2	0.03	2	μA
				Full		-7		7	
Digital Control Inputs (IN1, IN2, EN)⁽²⁾									
Input logic high	V_{IH}		Full	3.6 V	1.2		3.6	V	
Input logic low	V_{IL}		Full	3.6 V	0		0.65	V	
Input leakage current	I_{IH} , I_{IL}	$V_I = V_+$ or 0	25°C	3.6 V	-0.1	0.05	0.1	μA	
			Full		-2.5		2.5		
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 19	25°C	3 V to 3.6 V	18.1	59	ns	
				-40°C to 85°C			60		
				85°C to 105°C			68		
Turn-off time	t_{OFF}	$V_{COM} = V_+$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 19	25°C	3 V to 3.6 V	25.4	60.6	ns	
				-40°C to 85°C			61		
				85°C to 105°C			70		
Break-before- make time	t_{BBM}	$V_{NC} = V_{NO} = V_+/2$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 20	25°C	3.3 V	4	11.1	22.7	ns
				Full	3 V to 3.6 V			28	
Charge injection	Q_C	$V_{GEN} = 0$, $R_{GEN} = 0$,	$C_L = 0.1\text{ nF}$, See Figure 24	25°C	3.3 V		0.81	pC	
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch OFF,	See Figure 18	25°C	3.3 V		13	pF	
COM OFF capacitance	$C_{COM(OFF)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch OFF,	See Figure 18		3.3 V		8.5	pF	
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch OFF,	See Figure 18	25°C	3.3 V		21.5	pF	
COM ON capacitance	$C_{COM(ON)}$	$V_{COM} = V_+$ or GND, Switch ON,	See Figure 18	25°C	3.3 V		21.5	pF	

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾ (continued)

V₊ = 3 V to 3.6 V, T_A = –40°C to 105°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Digital input capacitance	C _I	V _I = V ₊ or GND See Figure 18	25°C	3.3 V		2		pF
Bandwidth	BW	R _L = 50 Ω, Switch ON, See Figure 20	25°C	3.3 V		240		MHz
OFF isolation	O _{ISO}	R _L = 50 Ω, f = 10 MHz, Switch OFF, See Figure 22	25°C	3.3 V		–62		dB
Crosstalk	X _{TALK}	R _L = 50 Ω, f = 10 MHz, Switch ON, See Figure 23	25°C	3.3 V		–62		dB
Crosstalk adjacent	X _{TALK(ADJ)}	R _L = 50 Ω, f = 10 MHz, Switch ON, See Figure 23	25°C	3.3 V		–71		dB
Total harmonic distortion	THD	R _L = 600 Ω, C _L = 50 pF, f = 20 Hz to 20 kHz, See Figure 25	25°C	3.3 V		0.05		%
Supply								
Positive supply current	I ₊	V _I = V ₊ or GND, Switch ON or OFF	25°C	3.6 V		0.04	0.3	μA
			–40°C to 85°C				3	
			85°C to 105°C				5	

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾

V₊ = 2.3 V to 2.7 V, T_A = –40°C to 105°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	V _{COM} , V _{NO} , V _{NC}				0		V ₊	Ω
ON-state resistance	r _{on}	0 ≤ (V _{NC} or V _{NO}) ≤ V ₊ , I _{COM} = –32 mA, Switch ON, See Figure 15	25°C	2.3 V		5.5	9.6	Ω
			Full				11.5	
ON-state resistance match between channels	Δr _{on}	V _{NC} or V _{NO} = 1.6 V, I _{COM} = –32 mA, Switch ON, See Figure 15	25°C	2.3 V		0.3	0.8	Ω
			Full				0.9	
ON-state resistance flatness	r _{on(flat)}	0 ≤ (V _{NC} or V _{NO}) ≤ V ₊ , I _{COM} = –32 mA, Switch ON, See Figure 16	25°C	2.3 V		0.91	2.2	Ω
			Full				2.3	
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	V _{NC} or V _{NO} = 0.5 V, V _{COM} = 2.3 V, or V _{NC} or V _{NO} = 2.3 V, V _{COM} = 0.5 V, Switch OFF, See Figure 16	25°C	2.7 V		–0.3	0.04	μA
			Full				–6	
	I _{NC(PWROFF)} , I _{NO(PWROFF)}	V _{NC} or V _{NO} = 0 to 2.7 V, V _{COM} = 2.7 V to 0, or V _{NC} or V _{NO} = 2.7 V to 0, V _{COM} = 0 to 2.7 V,	25°C	0 V		–0.6	0.02	
COM OFF leakage current	I _{COM(OFF)}	V _{NC} or V _{NO} = 0.5 V, V _{COM} = 2.3 V, or V _{NC} or V _{NO} = 2.3 V, V _{COM} = 0.5 V, Switch OFF, See Figure 16	25°C	2.7 V		–0.7	0.02	μA
			Full				–1	
	I _{COM(PWROFF)}	V _{NC} or V _{NO} = 2.7 V to 0, V _{COM} = 0 to 2.7 V, or V _{NC} or V _{NO} = 0 to 2.7 V, V _{COM} = 2.7 V to 0,	25°C	0 V		–0.7	0.02	
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	V _{NC} or V _{NO} = 0.5 V or 2.3 V, V _{COM} = Open, Switch ON, See Figure 17	25°C	2.7 V		–2.1	0.03	μA
			Full				–6	
COM ON leakage current	I _{COM(ON)}	V _{NC} or V _{NO} = Open, V _{COM} = 0.5 V, or V _{NC} or V _{NO} = Open, V _{COM} = 2.3 V, Switch ON, See Figure 17	25°C	2.7 V		–2	0.02	μA
			Full				–5.7	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾ (continued)
 $V_+ = 2.3 \text{ V to } 2.7 \text{ V}$, $T_A = -40^\circ\text{C to } 105^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT	
Digital Control Inputs (IN1, IN2, $\overline{\text{EN}}$)⁽²⁾									
Input logic high	V_{IH}	$V_I = V_+$ or GND	Full	2.7 V	1.15		3.6	V	
Input logic low	V_{IL}		Full	2.7 V	0		0.55	V	
Input leakage current	I_{IH}, I_{IL}	$V_I = V_+$ or 0	25°C	2.7 V		-0.1	0.01	0.1	
			Full						-2.1
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, $R_L = 50 \Omega$,	$C_L = 35 \text{ pF}$, See Figure 19	25°C	2.5 V		17.2	36.8	
				Full					2.3 V to 2.7 V
Turn-off time	t_{OFF}	$V_{COM} = V_+$, $R_L = 50 \Omega$,	$C_L = 35 \text{ pF}$, See Figure 19	25°C	2.3 V to 2.7 V		17.1	29.8	
				-40°C to 85°C					34.4
				85°C to 105°C					38.4
Break-before-make time	t_{BBM}	$V_{NC} = V_{NO} = V_+/2$, $R_L = 50 \Omega$,	$C_L = 35 \text{ pF}$, See Figure 20	25°C	2.5 V	4.5	13	30	
				Full					2.3 V to 2.7 V
Charge injection	Q_C	$V_{GEN} = 0$, $R_{GEN} = 0$,	$C_L = 0.1 \text{ nF}$, See Figure 24	25°C	2.5 V		0.47	pC	
NC, NO OFF capacitance	$C_{NC(OFF)}$, $C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch OFF,	See Figure 18	25°C	2.5 V		13.5	pF	
COM OFF capacitance	$C_{COM(OFF)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch OFF,	See Figure 18		2.5 V		9	pF	
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch OFF,	See Figure 18	25°C	2.5 V		22	pF	
COM ON capacitance	$C_{COM(ON)}$	$V_{COM} = V_+$ or GND, Switch ON,	See Figure 18	25°C	2.5 V		22	pF	
Digital input capacitance	C_I	$V_I = V_+$ or GND	See Figure 18	25°C	2.5 V		2	pF	
Bandwidth	BW	$R_L = 50 \Omega$,	Switch ON, See Figure 20	25°C	2.5 V		240	MHz	
OFF isolation	O_{ISO}	$R_L = 50 \Omega$, $f = 10 \text{ MHz}$,	Switch OFF, See Figure 22	25°C	2.5 V		-62	dB	
Crosstalk	X_{TALK}	$R_L = 50 \Omega$, $f = 10 \text{ MHz}$,	Switch ON, See Figure 23	25°C	2.5 V		-62	dB	
Crosstalk adjacent	$X_{TALK(ADJ)}$	$R_L = 50 \Omega$, $f = 10 \text{ MHz}$,	Switch ON, See Figure 23	25°C	2.5 V		-71	dB	
Total harmonic distortion	THD	$R_L = 600 \Omega$, $C_L = 50 \text{ pF}$,	$f = 20 \text{ Hz to } 20 \text{ kHz}$, See Figure 25	25°C	2.5 V		0.06	%	
Supply									
Positive supply current	I_+	$V_I = V_+$ or GND,	Switch ON or OFF	25°C	2.7 V		0.01	0.1	
				-40°C to 85°C					2
				85°C to 105°C					3

(2) All unused digital inputs of the device must be held at V_+ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY⁽¹⁾
 $V_+ = 1.65 \text{ V to } 1.95 \text{ V}$, $T_A = -40^\circ\text{C to } 105^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	V_{COM} , V_{NO} , V_{NC}				0		V_+	Ω
ON-state resistance	r_{on}	$0 \leq (V_{NC} \text{ or } V_{NO}) \leq V_+$, $I_{COM} = -32 \text{ mA}$,	Switch ON, See Figure 15	25°C	1.65 V		7.1	14.4
				Full				

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY⁽¹⁾ (continued)

V₊ = 1.65 V to 1.95 V, T_A = –40°C to 105°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
ON-state resistance match between channels	Δr _{on}	V _{NC} or V _{NO} = 1.5 V, I _{COM} = –32 mA, Switch ON, See Figure 15	25°C	1.65 V	0.3		1	Ω
			Full				1.2	
ON-state resistance flatness	r _{on(flat)}	0 ≤ (V _{NC} or V _{NO}) ≤ V ₊ , I _{COM} = –32 mA, Switch ON, See Figure 16	25°C	1.65 V	2.7		5.5	Ω
			Full				7.3	
NC, NO OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	V _{NC} or V _{NO} = 0.3 V, V _{COM} = 1.65 V, or V _{NC} or V _{NO} = 1.65 V, V _{COM} = 0.3 V, Switch OFF, See Figure 16	25°C	1.95 V	–0.25	0.03	0.25	μA
			Full		–5		5	
	I _{NC(PWROFF)} , I _{NO(PWROFF)}	V _{NC} or V _{NO} = 1.95 V to 0, V _{COM} = 0 to 1.95 V, or V _{NC} or V _{NO} = 0 to 1.95 V, V _{COM} = 1.95 V to 0, Switch OFF, See Figure 16	25°C	0 V	–0.4	0.01	0.4	μA
			Full		–7.2		7.2	
COM OFF leakage current	I _{COM(OFF)} , I _{COM(OFF)}	V _{NC} or V _{NO} = 0.3 V, V _{COM} = 1.65 V, or V _{NC} or V _{NO} = 1.65 V, V _{COM} = 0.3 V, Switch OFF, See Figure 16	25°C	1.95 V	–0.4	0.02	0.4	μA
			Full		–0.9		0.9	
	I _{COM(PWROFF)} , I _{COM(PWROFF)}	V _{NC} or V _{NO} = 1.95 V to 0, V _{COM} = 0 to 1.95 V, or V _{NC} or V _{NO} = 0 to 1.95 V, V _{COM} = 1.95 V to 0, Switch OFF, See Figure 16	25°C	0 V	–0.4	0.02	0.4	μA
			–40°C to 85°C		–5		5	
			85°C to 105°C	–5.8		5.8		
NC, NO ON leakage current	I _{NO(ON)} , I _{NC(ON)}	V _{NC} or V _{NO} = 0.3 V, V _{COM} = Open, or V _{NC} or V _{NO} = 1.65 V, V _{COM} = Open, Switch ON, See Figure 17	25°C	1.95 V	–2	0.02	2	μA
			Full		–5.2		5.2	
COM ON leakage current	I _{COM(ON)}	V _{NC} or V _{NO} = Open, V _{COM} = 0.3 V, or V _{NC} or V _{NO} = Open, V _{COM} = 1.65 V, Switch ON, See Figure 17	25°C	1.95 V	–2	0.02	2	μA
			Full		–5.2		5.2	
Digital Control Inputs (IN1, IN2, EN)⁽²⁾								
Input logic high	V _{IH}	V _I = V ₊ or GND	Full	1.95 V	1		3.6	V
Input logic low	V _{IL}		Full	1.95 V	0		0.4	V
Input leakage current	I _{IH} , I _{IL}	V _I = V ₊ or 0	25°C	1.95 V	–0.1	0.01	0.1	μA
			Full		–2.1		2.1	
Dynamic								
Turn-on time	t _{ON}	V _{COM} = V ₊ , R _L = 50 Ω, C _L = 35 pF, See Figure 19	25°C	1.8 V	14.1		49.3	ns
			Full	1.65 V to 1.95 V			56.7	
Turn-off time	t _{OFF}	V _{COM} = V ₊ , R _L = 50 Ω, C _L = 35 pF, See Figure 19	25°C	1.8 V	16.1		26.5	ns
			–40°C to 85°C	1.65 V to 1.95 V			31.2	
			85°C to 105°C				35.2	
Break-before-make time	t _{BBM}	V _{NC} = V _{NO} = V ₊ /2, R _L = 50 Ω, C _L = 35 pF, See Figure 20	25°C	1.8 V	5.3	18.4	58	ns
			Full	1.65 V to 1.95 V			58	
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0, C _L = 1 nF, See Figure 24	25°C	1.8 V	0.21		pC	
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF, See Figure 18	25°C	1.8 V	9		pF	
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF, See Figure 18	25°C	1.8 V	22		pF	

(2) All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 1.8-V SUPPLY⁽¹⁾ (continued)
 $V_+ = 1.65\text{ V to }1.95\text{ V}$, $T_A = -40^\circ\text{C to }105^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
COM ON capacitance	$C_{\text{COM(ON)}}$	$V_{\text{COM}} = V_+$ or GND, Switch ON,	See Figure 18	25°C	1.8 V		22		pF
Digital input capacitance	C_I	$V_I = V_+$ or GND	See Figure 18	25°C	1.8 V		2		pF
Bandwidth	BW	$R_L = 50\ \Omega$,	Switch ON, See Figure 20	25°C	1.8 V		240		MHz
OFF isolation	O_{ISO}	$R_L = 50\ \Omega$, $f = 10\text{ MHz}$,	Switch OFF, See Figure 22	25°C	1.8 V		-60		dB
Crosstalk	X_{TALK}	$R_L = 50\ \Omega$, $f = 10\text{ MHz}$,	Switch ON, See Figure 23	25°C	1.8 V		-60		dB
Crosstalk adjacent	$X_{\text{TALK(ADJ)}}$	$R_L = 50\ \Omega$, $f = 10\text{ MHz}$,	Switch ON, See Figure 23	25°C	1.8 V		-71		dB
Total harmonic distortion	THD	$R_L = 600\ \Omega$, $C_L = 50\text{ pF}$,	$f = 20\text{ Hz to }20\text{ kHz}$, See Figure 25	25°C	1.8 V		0.1		%
Supply									
Positive supply current	I_+	$V_I = V_+$ or GND,	Switch ON or OFF	25°C	1.95 V	0.01	0.1		μA
				-40°C to 85°C			1.5		
				85°C to 105°C			2.5		

Table 3. PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V_{COM}	Voltage at COM
V_{NC}	Voltage at NC
V_{NO}	Voltage at NO
r_{on}	Resistance between COM and NC or NO ports when the channel is ON
Δr_{on}	Difference of r_{on} between channels in a specific device
$r_{on(Flat)}$	Difference between the maximum and minimum value of r_{on} in a channel over the specified range of conditions
$I_{NC(OFF)}$	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state
$I_{NC(ON)}$	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) open
$I_{NO(OFF)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state
$I_{NO(ON)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
$I_{COM(OFF)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the OFF state
$I_{COM(ON)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NC or NO) in the ON state and the output (NC or NO) open
V_{IH}	Minimum input voltage for logic high for the control input (IN, \overline{EN})
V_{IL}	Maximum input voltage for logic low for the control input (IN, \overline{EN})
V_I	Voltage at the control input (IN, \overline{EN})
I_{IH}, I_{IL}	Leakage current measured at the control input (IN, \overline{EN})
t_{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning ON.
t_{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (NC or NO) signal when the switch is turning OFF.
Q_C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC or NO) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance and ΔV_{COM} is the change in analog output voltage.
$C_{NC(OFF)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
$C_{NC(ON)}$	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
$C_{NO(ON)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
$C_{COM(OFF)}$	Capacitance at the COM port when the corresponding channel (COM to NC) is OFF
$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NC) is ON
C_I	Capacitance of control input (IN, \overline{EN})
O_{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedence. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM) in the OFF state.
X_{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC1 to NO1). Adjacent crosstalk is a measure of unwanted signal coupling from an ON channel to an adjacent ON channel (NC1 to NC2). This is measured in a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.
I_+	Static power-supply current with the control (IN) pin at V_+ or GND

TYPICAL CHARACTERISTICS

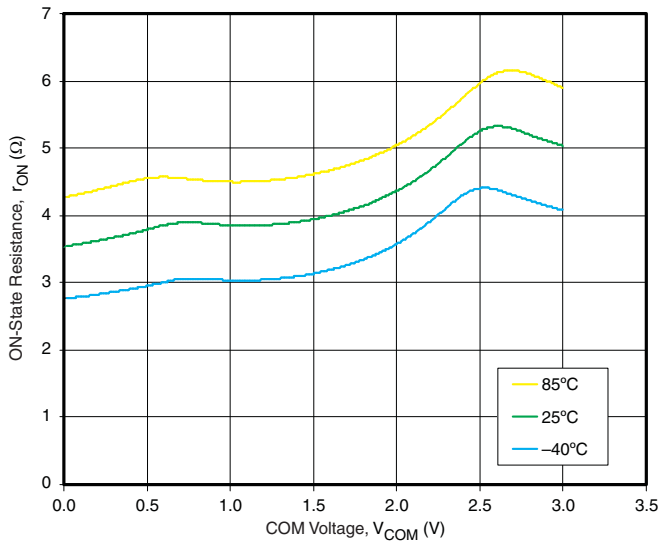


Figure 1. ON-State Resistance vs COM Voltage ($V_+ = 3\text{ V}$)

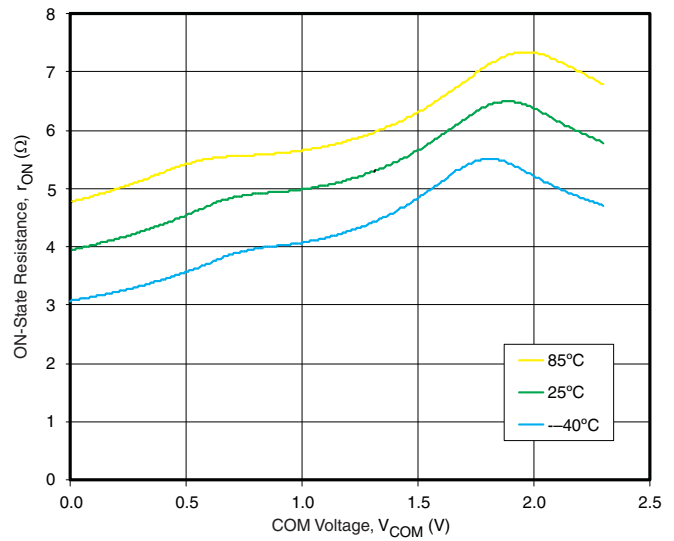


Figure 2. ON-State Resistance vs COM Voltage ($V_+ = 2.3\text{ V}$)

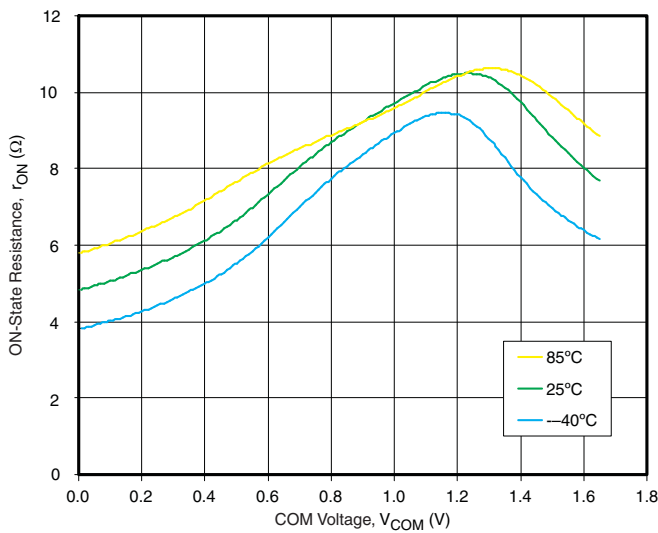


Figure 3. ON-State Resistance vs COM Voltage ($V_+ = 1.65\text{ V}$)

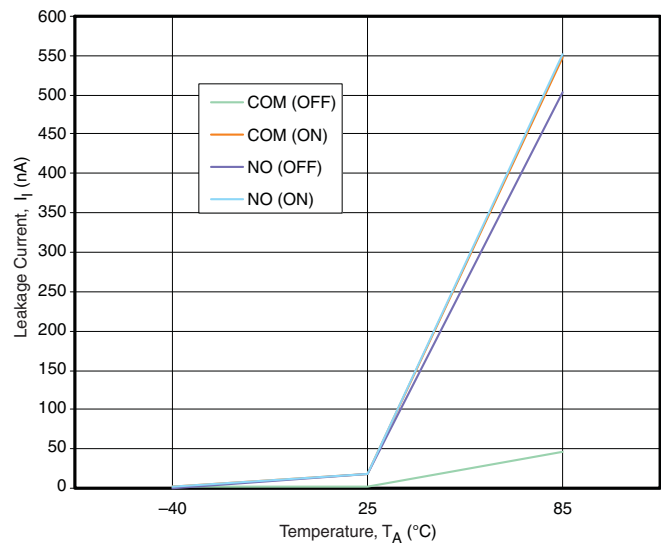


Figure 4. Leakage Current vs Temperature ($V_+ = 3.3\text{ V}$)

TYPICAL CHARACTERISTICS (continued)

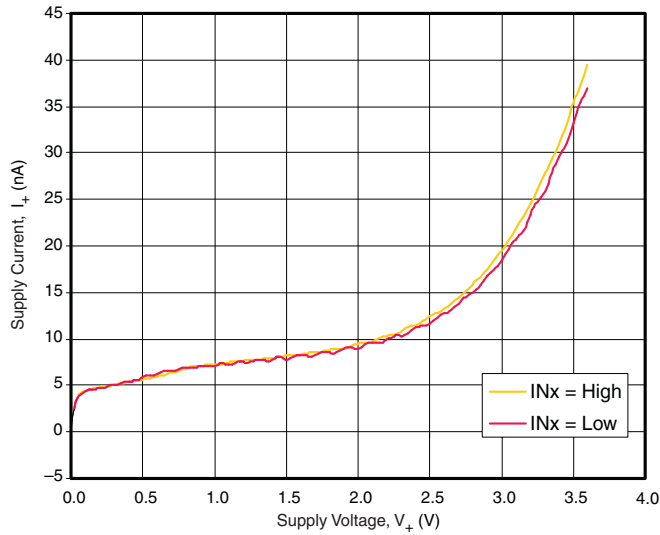


Figure 5. Supply Current vs Supply Voltage

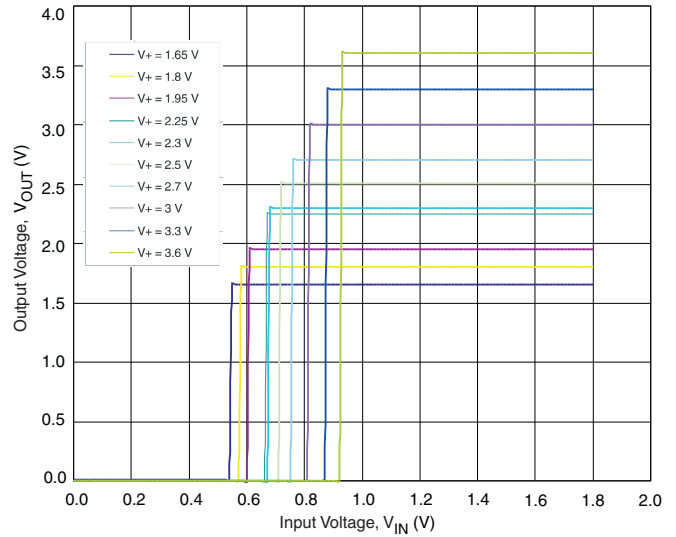


Figure 6. Control Input Thresholds (IN1, T_A = 25°C)

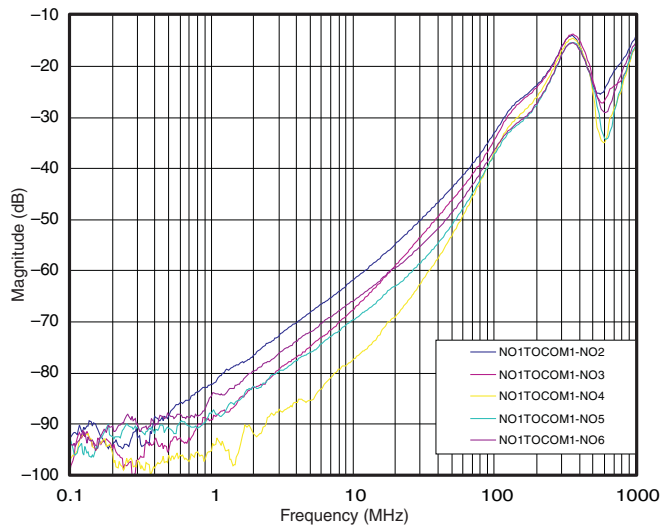


Figure 7. Crosstalk Adjacent

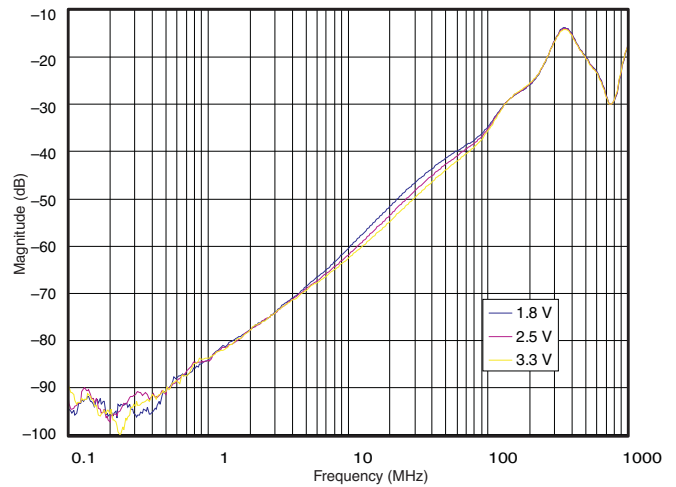


Figure 8. Crosstalk

TYPICAL CHARACTERISTICS (continued)

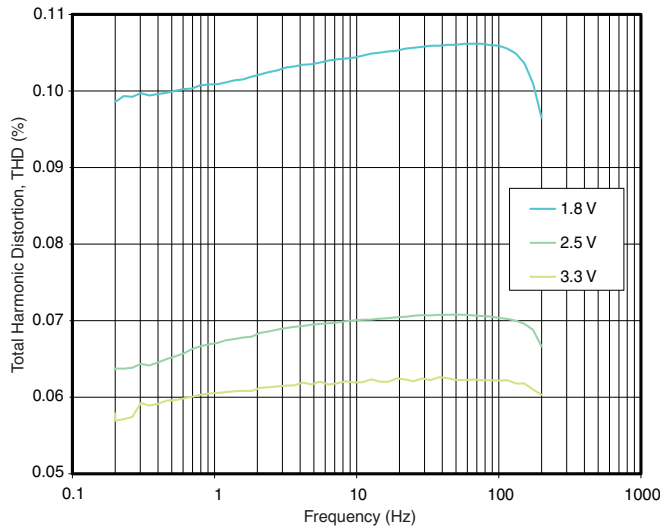


Figure 9. Total Harmonic Distortion vs Frequency

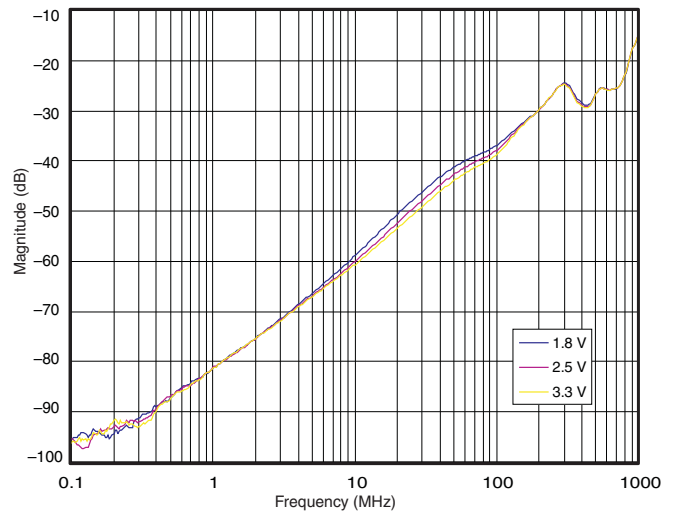


Figure 10. OFF Isolation

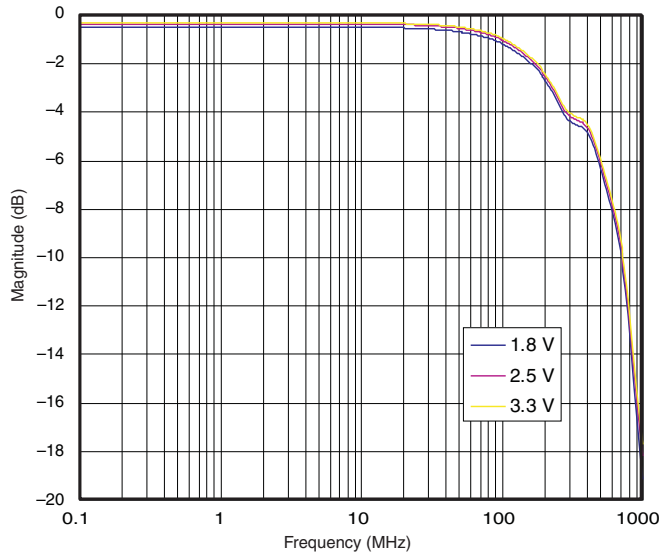


Figure 11. Insertion Loss

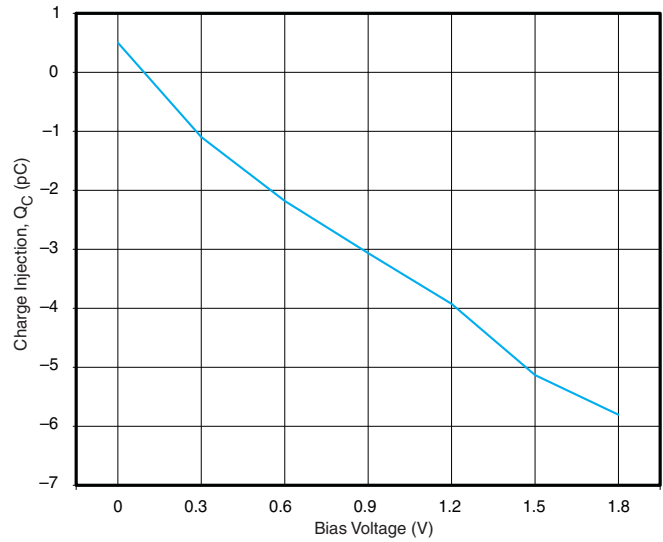


Figure 12. Charge Injection vs Bias Voltage (1.8 V)

TYPICAL CHARACTERISTICS (continued)

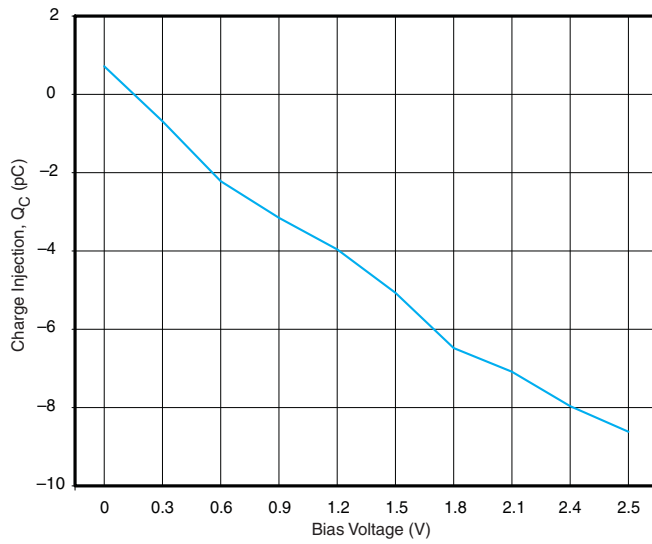


Figure 13. Charge Injection vs Bias Voltage (2.5 V)

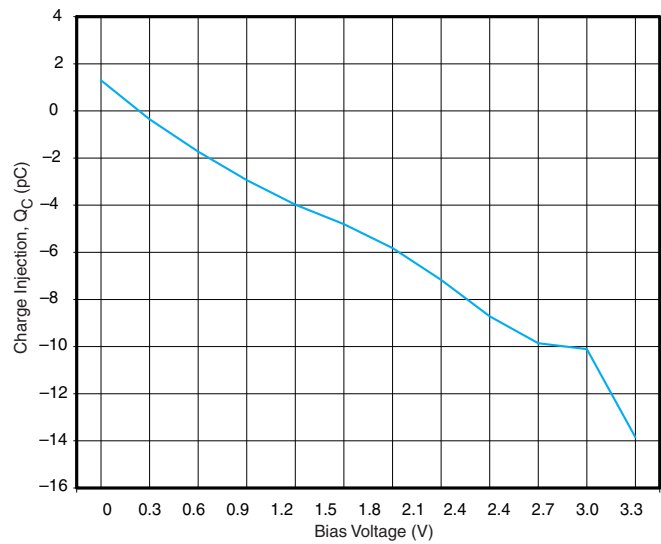


Figure 14. Charge Injection vs Bias Voltage (3.3 V)

PARAMETER MEASUREMENT INFORMATION

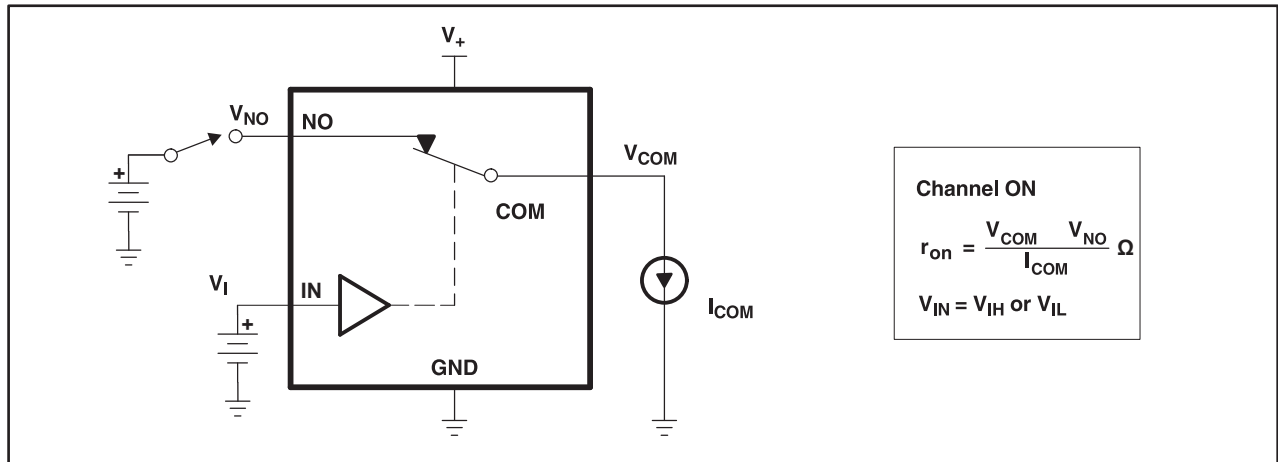


Figure 15. ON-state Resistance (r_{ON})

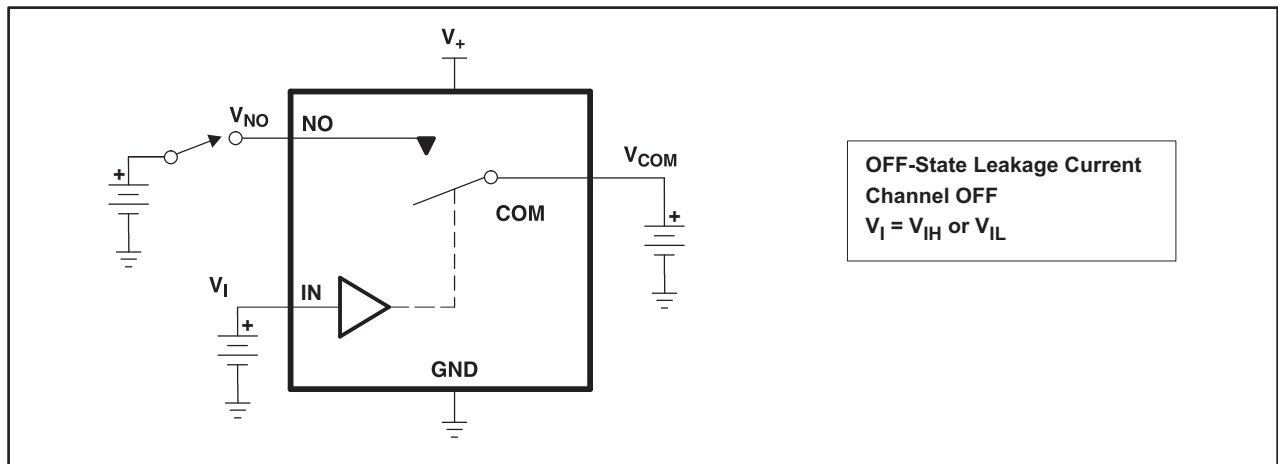


Figure 16. OFF-State Leakage Current
($I_{COM(OFF)}$, $I_{NC(OFF)}$, $I_{COM(PWROFF)}$, $I_{NC(PWROFF)}$)

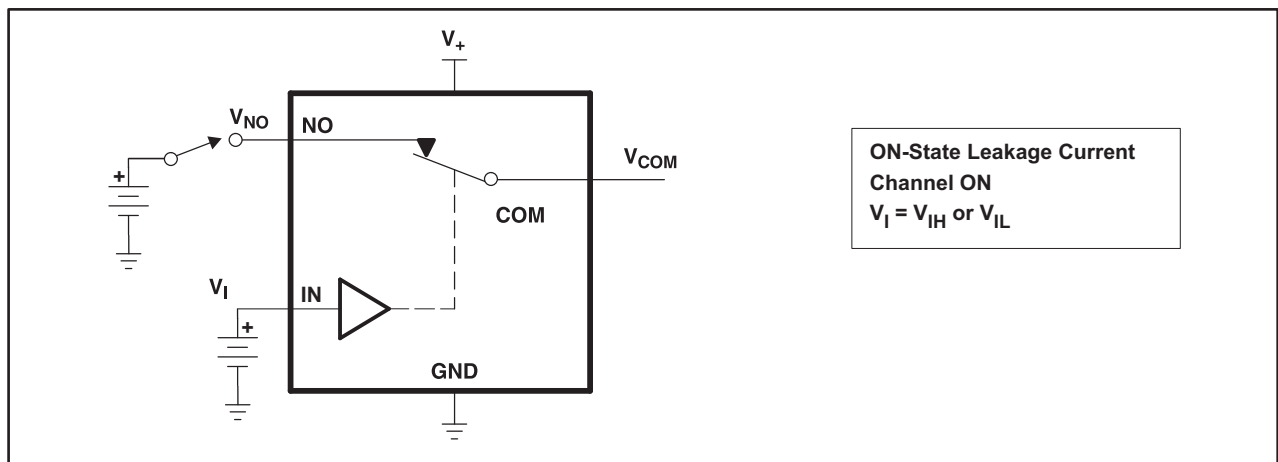


Figure 17. ON-State Leakage Current
($I_{COM(ON)}$, $I_{NC(ON)}$)

PARAMETER MEASUREMENT INFORMATION (continued)

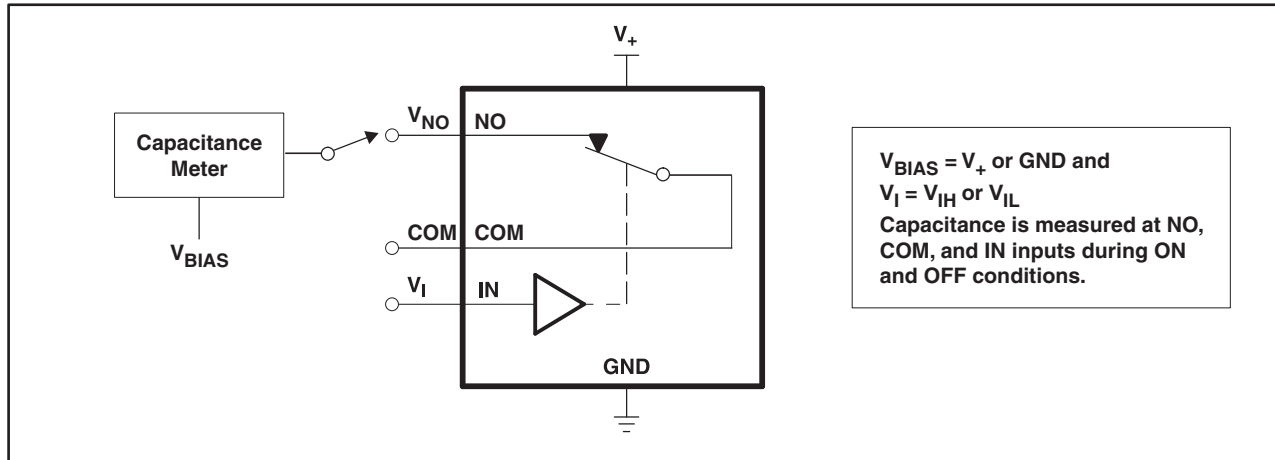


Figure 18. Capacitance
(C_I , $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)

- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

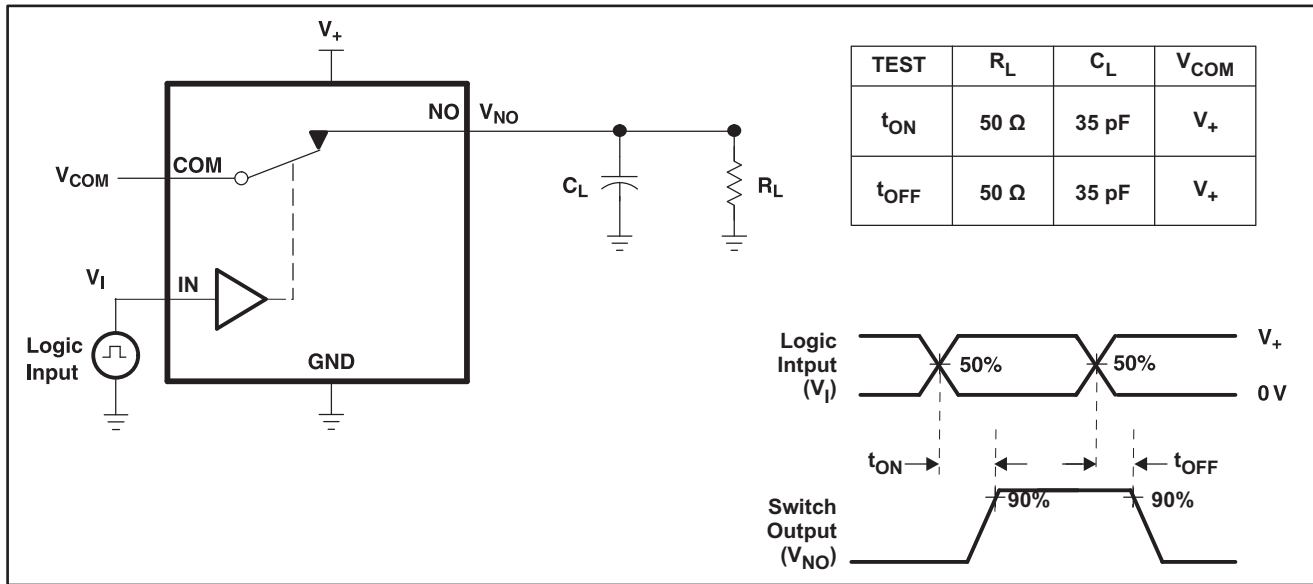


Figure 19. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})

- A. C_L includes probe and jig capacitance.
- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.

PARAMETER MEASUREMENT INFORMATION (continued)

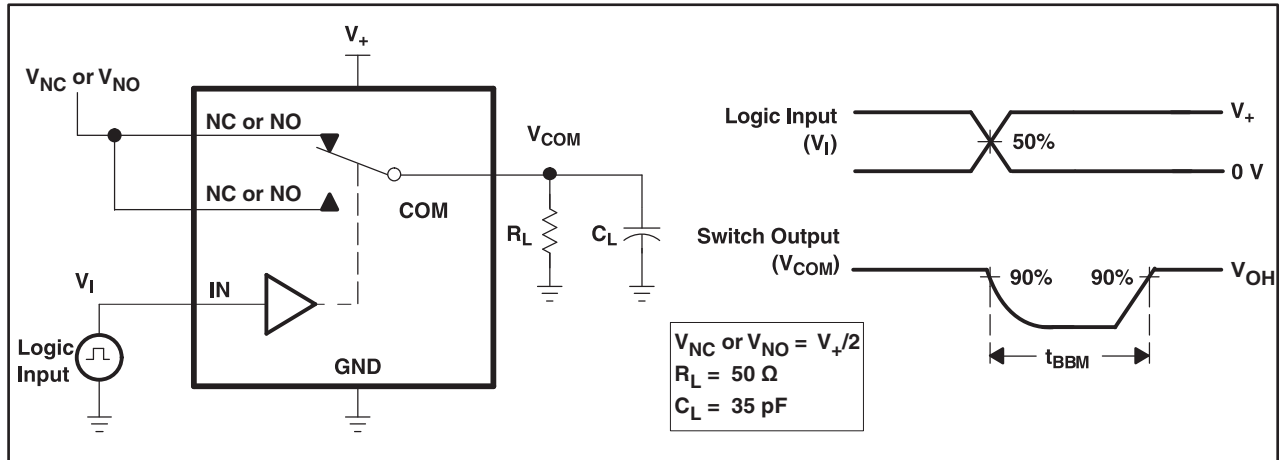


Figure 20. Break-Before-Make Time (t_{BBM})

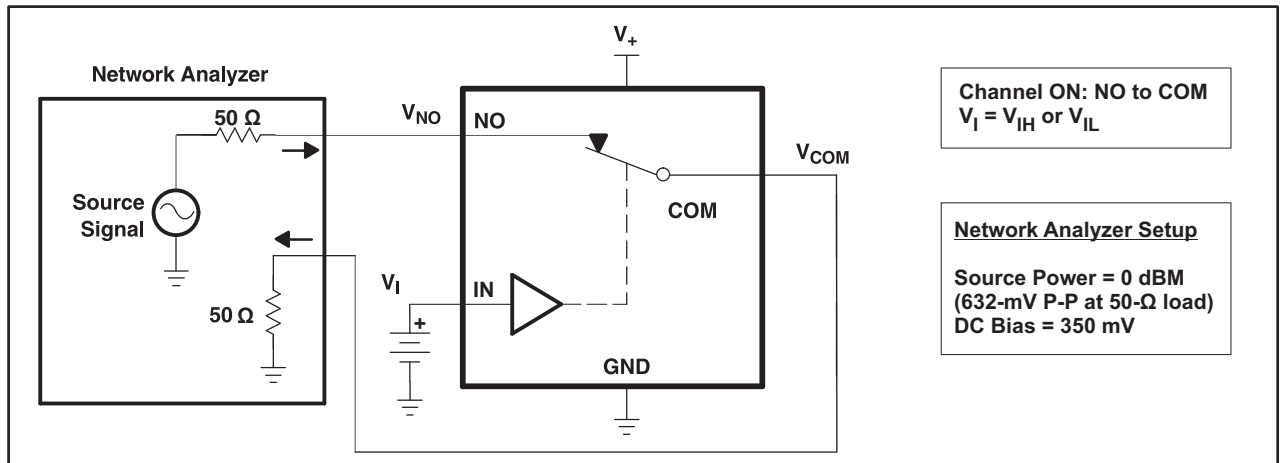


Figure 21. Bandwidth (BW)

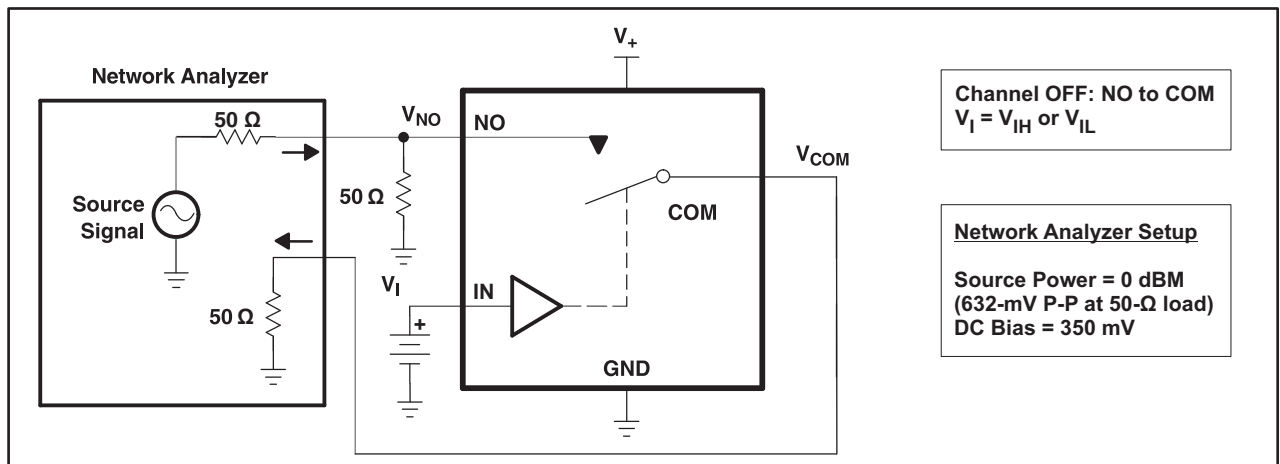


Figure 22. OFF Isolation (O_{ISO})

PARAMETER MEASUREMENT INFORMATION (continued)

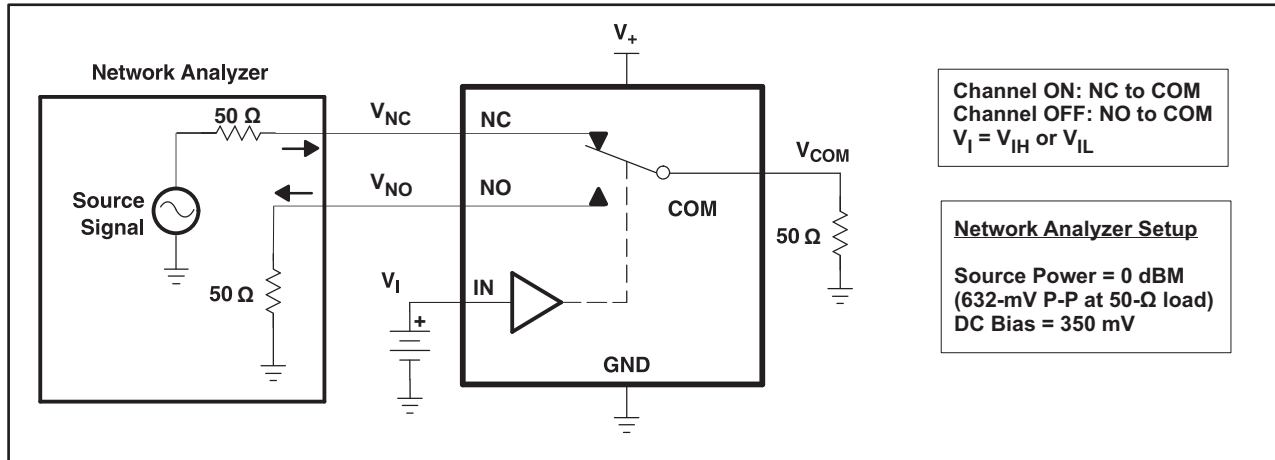


Figure 23. Crosstalk (X_{TALK})

- A. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10$ MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

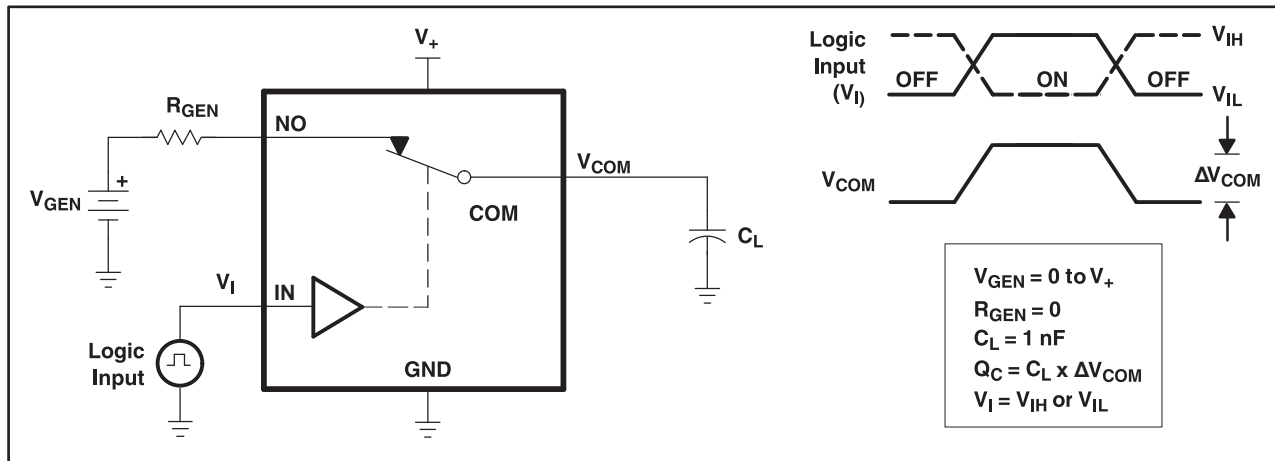


Figure 24. Charge Injection (Q_C)

- A. C_L includes probe and jig capacitance.

PARAMETER MEASUREMENT INFORMATION (continued)

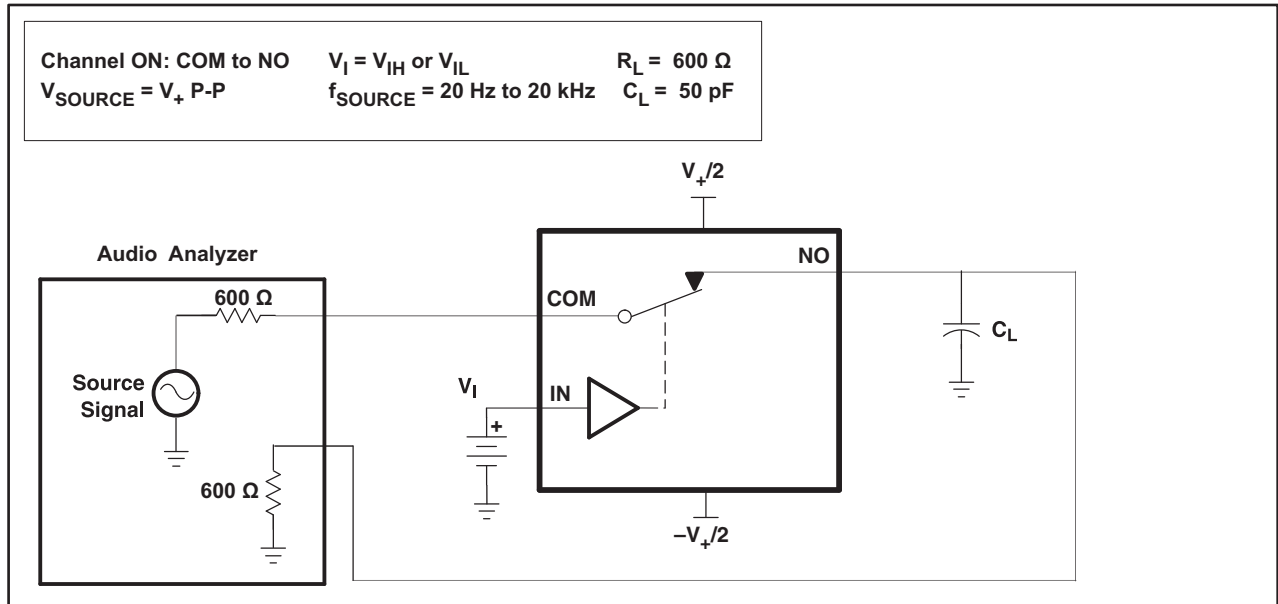


Figure 25. Total Harmonic Distortion (THD)

REVISION HISTORY

Changes from Revision A (March 2012) to Revision B	Page
• Changed device temp grade from 1 to 2, removed maximum withstand voltage info, changed C3B2 to C3B.	1
• Added extra row to ordering information table.	2
• Changed $T_A = -40^\circ\text{C}$ to 85°C to $T_A = -40^\circ\text{C}$ to 105°C	4
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C and limits -7.5 to 7.5	5
• Changed $T_A = -40^\circ\text{C}$ to 85°C to $T_A = -40^\circ\text{C}$ to 105°C	5
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C with limits 68	5
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C with limits 70	5
• Changed $T_A = -40^\circ\text{C}$ to 85°C to $T_A = -40^\circ\text{C}$ to 105°C	6
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C with limits 5 μA	6
• Changed $T_A = -40^\circ\text{C}$ to 85°C to $T_A = -40^\circ\text{C}$ to 105°C	6
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C with limits 38.4	7
• Changed $T_A = -40^\circ\text{C}$ to 85°C to $T_A = -40^\circ\text{C}$ to 105°C	7
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C with limits 3	7
• Changed $T_A = -40^\circ\text{C}$ to 85°C to $T_A = -40^\circ\text{C}$ to 105°C	7
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C and limits -5.8 to 5.8	8
• Changed $T_A = -40^\circ\text{C}$ to 85°C to $T_A = -40^\circ\text{C}$ to 105°C	8
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C with limits 35.2	8
• Changed $T_A = -40^\circ\text{C}$ to 85°C to $T_A = -40^\circ\text{C}$ to 105°C	9
• Changed Full to -40°C to 85°C and added extra row with 85°C to 105°C with limits 2.5	9

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TS3A27518EIPWRQ1	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	
TS3A27518EIRTWRQ1	ACTIVE	WQFN	RTW	24	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	
TS3A27518ETRTWRQ1	ACTIVE	WQFN	RTW	24	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TS3A27518E-Q1 :

- Catalog: [TS3A27518E](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3A27518EIPWRQ1	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
TS3A27518EIRTWRQ1	WQFN	RTW	24	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
TS3A27518ETRTWRQ1	WQFN	RTW	24	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3A27518EIPWRQ1	TSSOP	PW	24	2000	367.0	367.0	38.0
TS3A27518EIRTWRQ1	WQFN	RTW	24	3000	367.0	367.0	35.0
TS3A27518ETRTWRQ1	WQFN	RTW	24	3000	367.0	367.0	35.0

PW (R-PDSO-G24)

PLASTIC SMALL OUTLINE

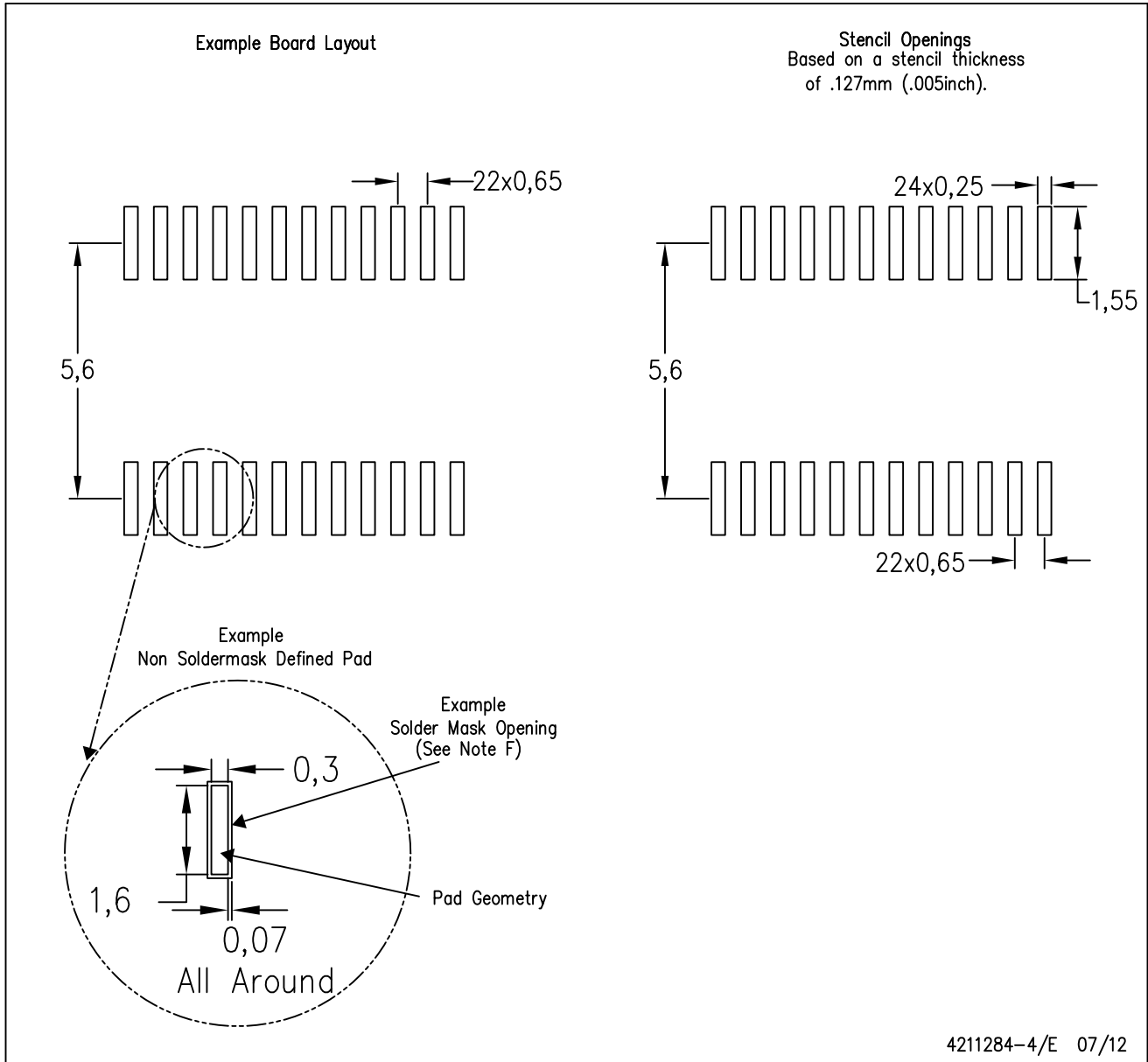


4040064-6/G 02/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 - Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153

PW (R-PDSO-G24)

PLASTIC SMALL OUTLINE



4211284-4/E 07/12

- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate design.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

RTW (S-PWQFN-N24)

PLASTIC QUAD FLATPACK NO-LEAD



4206244/C 07/11

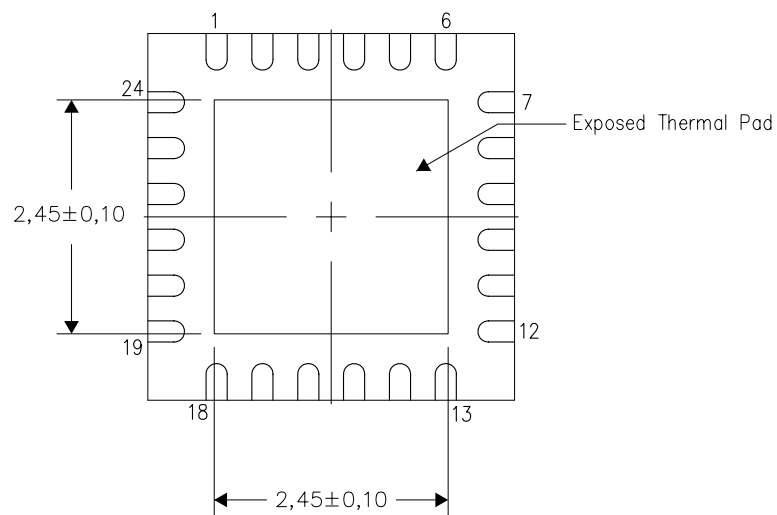
- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - Quad Flatpack, No-Leads (QFN) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
 - Falls within JEDEC MO-220.

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

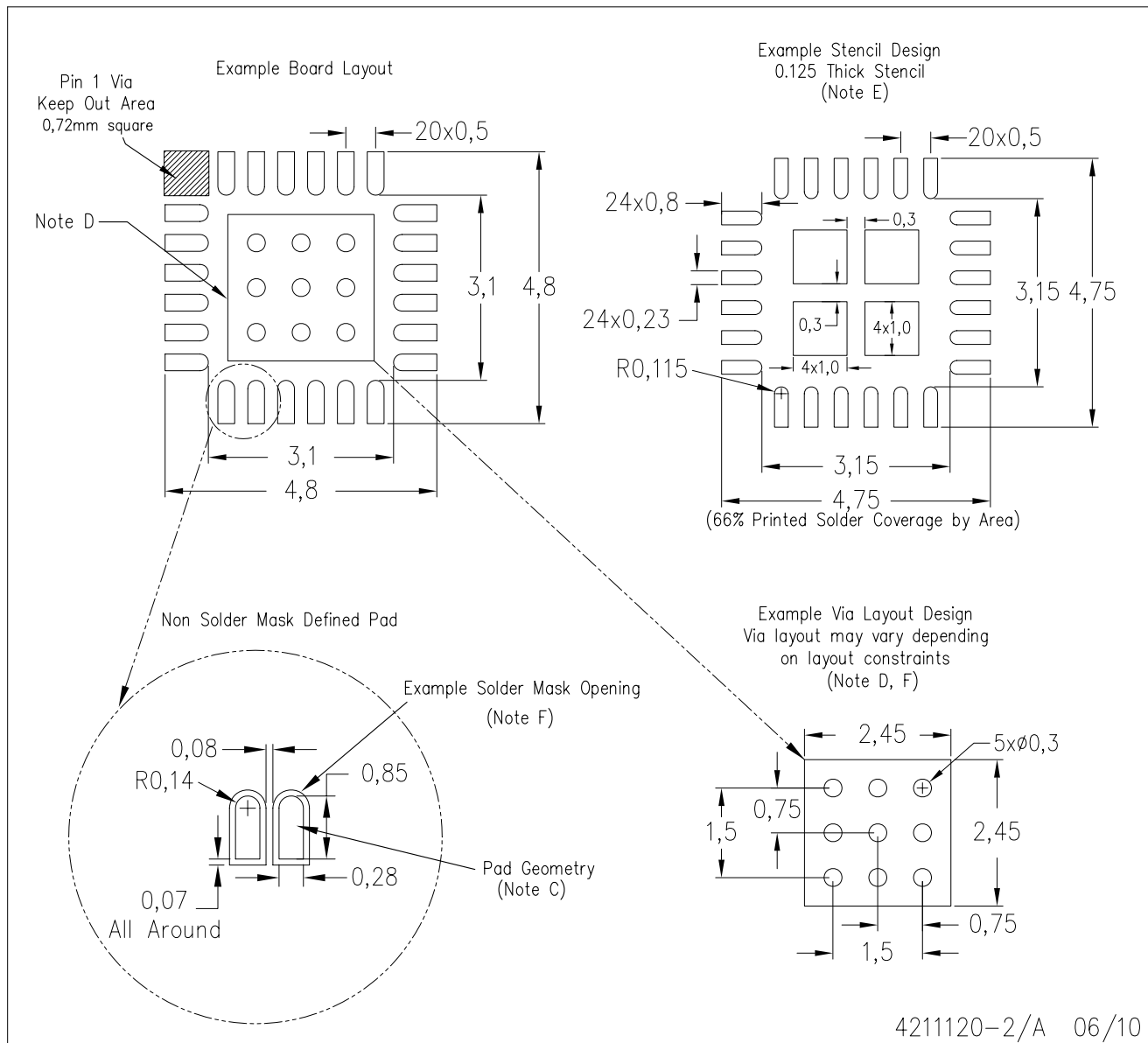
Exposed Thermal Pad Dimensions

4206249-3/L 07/11

NOTES: A. All linear dimensions are in millimeters

RTW (S-PWQFN-N24)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46C and to discontinue any product or service per JESD48B. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components which meet ISO/TS16949 requirements, mainly for automotive use. Components which have not been so designated are neither designed nor intended for automotive use; and TI will not be responsible for any failure of such components to meet such requirements.

Products

Audio	www.ti.com/audio
Amplifiers	amplifier.ti.com
Data Converters	dataconverter.ti.com
DLP® Products	www.dlp.com
DSP	dsp.ti.com
Clocks and Timers	www.ti.com/clocks
Interface	interface.ti.com
Logic	logic.ti.com
Power Mgmt	power.ti.com
Microcontrollers	microcontroller.ti.com
RFID	www.ti-rfid.com
OMAP Mobile Processors	www.ti.com/omap
Wireless Connectivity	www.ti.com/wirelessconnectivity

Applications

Automotive and Transportation	www.ti.com/automotive
Communications and Telecom	www.ti.com/communications
Computers and Peripherals	www.ti.com/computers
Consumer Electronics	www.ti.com/consumer-apps
Energy and Lighting	www.ti.com/energy
Industrial	www.ti.com/industrial
Medical	www.ti.com/medical
Security	www.ti.com/security
Space, Avionics and Defense	www.ti.com/space-avionics-defense
Video and Imaging	www.ti.com/video

TI E2E Community e2e.ti.com